



**UNIVERSITI PUTRA MALAYSIA**

***CHARACTERIZATION OF  $ZnXCd_{1-X}S$  TERNARY SEMICONDUCTOR  
NANOPARTICLES SYNTHESIZED BY MICROWAVE-ASSISTED  
HYDROTHERMAL TECHNIQUE***

**MINA ASKARI VERNOSFADERANI**

**FS 2014 98**



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HYDROTHERMAL TECHNIQUE**

**By**

**MINA ASKARI VERNOSFADERANI**

**Thesis Submitted to the School of Graduate Studies, Universiti Putra Malaysia,  
in Fulfillment of the Requirements for the Degree of Master of Science**

**July 2014**

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## DEDICATION

*I lovingly dedicate this thesis to my husband, Mahdi, who supported me  
each step of the way and remains willing to engage with the struggle,*

*My dear family, for being so supportive,*

*and my sweetheart daughter Gisu*



Abstract of thesis presented to the Senate of Universiti Putra Malaysia in fulfilment  
of the requirement for the degree of Master of Science

# CHARACTERIZATION OF $\text{Zn}_x\text{Cd}_{1-x}\text{S}$ TERNARY SEMICONDUCTOR NANOPARTICLES SYNTHESIZED BY MICROWAVE-ASSISTED HYDROTHERMAL TECHNIQUE

By

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**July 2014**

**Chairman: Professor Elias Saion, PhD**

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In this work, the microwave-assisted hydrothermal method was used to synthesize  $\text{Zn}_x\text{Cd}_{1-x}\text{S}$  ternary quantum dots. In order to study the effect of different stoichiometries on  $\text{Zn}_x\text{Cd}_{1-x}\text{S}$  properties, the molar ratio of Zn/Cd was chosen as 0.1/0.9, 0.3/0.7, 0.5/0.5, 0.7/0.3, and 0.9/0.1, and to use semiconductor quantum dots in technology, the stability of these materials is very important and can be achieved by capping the particles with either organic or inorganic materials like polymers. Zinc chloride ( $\text{ZnCl}_2$ ), cadmium chloride ( $\text{CdCl}_2$ ), and sodium sulfide ( $\text{Na}_2\text{S}$ ) were used as Zn, Cd, and S sources respectively, and polyvinylpyrrolidone (PVP) and thioglycolic acid (TGA) were used as capping agent and stabilizer to control particle's growth and distilled water as a solvent. The solution was heated in a microwave oven with 100% power for 4 minutes and the resulting precipitation was centrifuged, washed, and dried at 100 °C for 24 hours. By increasing the value of x from 0.1 to x=0.9, the powder color changed from dark yellow to white as verified by X-ray diffraction (XRD). The average particle sizes of  $\text{Zn}_x\text{Cd}_{1-x}\text{S}$  nanoparticles as deduced from Scherrer's equation by XRD peaks and from the images of transmission electron microscopy (TEM) were found to vary within range 3-5 nm with x values. The optical band gap energy in the range of 2.3 to 2.93 eV was calculated by Tauc plot of the UV-visible spectra. The band gap has increased with increasing the value of x due to a decrease in particle size.

The synthesized  $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$  quantum dots capped by TGA and PVP have band gaps between 2.93 to 3.43, and 2.91 to 2.98 respectively. PL spectra for  $\text{Zn}_x\text{Cd}_{1-x}\text{S}$  have three emission peaks related to sulfur, zinc, and cadmium vacancies respectively. The emission peaks II that belong to zinc vacancies are observed at 484, 483, 483, 481, and 478 nm that are shifted to the lower wavelengths by increasing the value of x, and correspond to 2.56, 2.57, 2.57, 2.58, and 2.6 (eV). This significant continuous shift is an evidence for the formation of the ternary  $\text{Zn}_x\text{Cd}_{1-x}\text{S}$  quantum dot, rather than forming separate CdS, ZnS, or core-shell nanoparticle structure.

Abstrak tesis yang dikemukakan kepada Senat Universiti Putra Malaysia  
Sebagai memenuhi keperluan untuk ijazah Master Sains

**PENCIRIAN  $Zn_xCd_{1-x}S$  TERNARY SEMIKONDUKTOR NANOPARTIKEL  
DISINTESIS OLEH MIKROWAVE-DIBANTU HIDROTERMA TEKNIK**

Oleh

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Dalam karya ini, kaedah hidroterma dibantu ketuhar gelombang mikro telah digunakan untuk mensintesis titik kuantum, nanopartikel ternary  $Zn_xCd_{1-x}S$ , ( $x = 0.1, 0.3, 0.5, 0.7$  dan  $0.9$ ). Zink klorida ( $ZnCl_2$ ), kadmium klorida ( $CdCl_2$ ) dan natrium sulfida ( $Na_2S$ ) telah digunakan sebagai sumber, Zn, Cd dan S masing-masing dan polyvinylpyrrolidone (PVP) dan asid thioglycolic (TGA) digunakan sebagai ejen menutup dan penstabil kepada pertumbuhan nanopartikel secara terkawal dan air suling sebagai pelarut. Larutan dipanaskan di dalam ketuhar gelombang mikro dengan kuasa 100% selama 4 minit dan mendakan yang terhasil mengalami emparan, dibasuh dan dikeringkan pada  $100^\circ C$  selama 24 jam. Dengan meningkatkan nilai  $x$  daripada 0.1 untuk  $x = 0.9$ , warna serbuk bertukar daripada kuning gelap kepada putih dan keristiliti zarah ditukar daripada struktur hexagon kepada struktur kubus seperti yang disahkan oleh belauan sinar-x (XRD). Saiz purata nanopartikel  $Zn_xCd_{1-x}S$  seperti yang ditentukan dari persamaan Sherrer oleh puncak XRD dan imej-imej transmisi elektron microscopy (Julai) didapati berada dalam julat 3-5 nm dengan pertambahan nilai  $x$ . Jurang jalur tenaga optik telah dikira dengan plot Tauc untuk cahaya UV-tampak. Jurang tenaga telah meningkat dengan peningkatan nilai  $x$  antara 2.75 dan 3.02 (eV). Sintesis  $Zn_xCd_{1-x}S$  dengan TGA dan PVP mendapati jurang tenaga antara 2.98 hingga 3.04 eV dan 2.90 hingga 3.21 masing-masing. Spektrum PL untuk  $Zn_xCd_{1-x}S$  mempunyai tiga puncak penyinaran yang berkaitan dengan sulfur, zink dan kadmium masing-masing. Puncak penyinaran II dipunyai untuk zink yang dapat dilihat di 484, 483, 483, 481, dan 478 yang akan berpindah ke gelombang lebih rendah dengan meningkatkan nilai  $x$ , dan sesuai dengan nilai 2.56, 2.57, 2.57, 2.58 dan 2.6 (eV) masing-masing.

This thesis was submitted to the Senate of Universiti Putra Malaysia and has been accepted as fulfilment of the requirement for the degree of Master of science. The members of the Supervisory Committee were as follows:

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# TABLE OF CONTENTS

	<u>Page</u>
<b>ABSTRACT</b>	i
<b>ABSTRAK</b>	iii
<b>APPROVAL</b>	iv
<b>DECLARATION</b>	vi
<b>LIST OF TABLES</b>	x
<b>LIST OF FIGURES</b>	xi
<b>LIST OF ABBREVIATIONS</b>	xiii
<b>LIST OF SYMBOLS</b>	xiv
 <b>CHAPTER</b>	
<b>1 INTRODUCTION</b>	<b>1</b>
1.1 Background of study	1
1.2 Problem statement	1
1.3 Study objective	2
1.4 Scope of study	2
1.5 Thesis outline	3
 <b>2 LITERATURE REVIEW</b>	<b>4</b>
2.1 Nanoscience	4
2.2 Quantum dots	5
2.3 Synthesis methods of ZnCdS	6
2.3.1 Gas-phase process	6
2.3.2 Hydrothermal method	6
2.3.3 Gas-solid reaction	7
2.3.4 Co-precipitation method	7
2.3.5 Chemical bath deposition	8
2.3.6 Solvothermal	8
2.3.7 Sol-gel method	9
 <b>3 THEORY</b>	<b>12</b>
3.1 Semiconductor	12
3.1.1 Band structure of semiconductor	12
3.1.2 Electrical Conductivity	13
3.1.3 Indirect-gap and Direct-gap semiconductors	14
3.2 Semiconductor nanoparticle	15
3.2.1 Confinement regime	15
3.2.2 Quantum Dot	16
3.2.3 Band-Gap in QD	16
3.3 Synthesis of nanoparticles	18
3.3.1 Growth and nucleation theory	19
3.3.2 Nucleation	19
3.3.3 Growth	20
3.3.4 Size control of nano particles	21
3.4 Microwave Irradiation	22

3.4.1	Effect of microwave radiation on materials	23
<b>4</b>	<b>METHODOLOGY</b>	<b>25</b>
4.1	Introduction	25
4.2	Synthesis method	25
4.3	Materials	25
4.4	Synthesis of $\text{Zn}_x\text{Cd}_{1-x}\text{S}$ semiconductor QDs	26
4.5	Synthesis of $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticles with TGA and PVP capping agents	28
4.6	Characterization techniques	31
4.6.1	X-ray diffraction	31
4.6.2	Transmission Electron Microscopy (TEM)	35
4.6.3	UV-visible absorption spectroscopy	37
4.6.4	Photoluminescence spectroscopy	38
<b>5</b>	<b>RESULTS AND DISCUSSION</b>	<b>41</b>
5.1	Introduction	41
5.2	Effect of different ratio of Zn/Cd on morphology structure and optical properties of $\text{Zn}_x\text{Cd}_{1-x}\text{S}$ ternary quantum dots	41
5.2.1	XRD data	42
5.2.2	TEM images and size distribution	50
5.2.3	UV-vis spectra	53
5.2.4	PL spectra	58
5.3	Effect of capping agents on $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticles	60
5.4	TGA capped $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticles	60
5.4.1	XRD patterns	60
5.4.2	TEM images and size distribution	62
5.4.3	UV-vis spectra	63
5.4.4	PL spectra	67
5.5	PVP capped $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticles	67
5.5.1	XRD patterns	68
5.5.2	TEM images and size distribution	69
5.5.3	UV-vis spectra	71
5.5.4	PL spectra	75
5.6	A comparison of TGA and PVP capped $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticles in properties	76
<b>6</b>	<b>CONCLUSION</b>	<b>78</b>
6.1	Conclusions	78
6.2	future work and recommendation	79
	<b>REFERENCES</b>	<b>80</b>
	<b>APPENDIX</b>	<b>84</b>
	<b>BIODATA OF STUDENT</b>	<b>85</b>
	<b>PUBLICATION</b>	<b>86</b>

## LIST OF TABLES

Table	Page
2.1 A summary of the different methods used to synthesize of ZnCdS quantum dot nanoparticles.	9
3.1 Electrical conductivity and charge carrier concentration of metals, semiconductors, and insulators.	13
4.1 Different mol of Zn and Cd for different value of x	28
4.2 Different amount of stabilizer in synthesis of Zn <sub>0.9</sub> Cd <sub>0.1</sub> S nanoparticles	29
5.2 XRD data of Zn <sub>x</sub> Cd <sub>1-x</sub> S nanoparticles	50
5.3 TEM data of Zn <sub>x</sub> Cd <sub>1-x</sub> S semiconductor nanoparticles	53
5.4. UV-vis data of Zn <sub>x</sub> Cd <sub>1-x</sub> S nanoparticles	57
5.5. PL data of Zn <sub>x</sub> Cd <sub>1-x</sub> S nanoparticle quantum dots	59
5.6 XRD data of Zn <sub>0.9</sub> Cd <sub>0.1</sub> S nanoparticles	61
5.7 TEM data of TGA capped Zn <sub>0.9</sub> Cd <sub>0.1</sub> S nanoparticles	63
5.8 UV-vis data of TGA capped Zn <sub>0.9</sub> Cd <sub>0.1</sub> S nanoparticles	67
5.9 XRD data of PVP capped Zn <sub>0.9</sub> Cd <sub>0.1</sub> S semiconductor quantum dots	69
5.10 TEM data of TGA capped Zn <sub>0.9</sub> Cd <sub>0.1</sub> S nanoparticles	70
5.11 UV-vis data of PVP capped Zn <sub>0.9</sub> Cd <sub>0.1</sub> S nanoparticles	74
5.12 PL data of PVP capped Zn <sub>0.9</sub> Cd <sub>0.1</sub> S semiconductor ternary quantum dots	76
5.1 Peak list of reference pattern (ICDD PDF 00-024-1137)	84

## LIST OF FIGURES

Figure	Page
2.1 The increased interest in quantum dot	5
3.1 Band scheme for semiconductor. Current can flow only if electrons have energy more than the energy of band gap - $E_g$ .	12
3.2 Energy vector diagram for direct-gap and indirect-gap semiconductors	14
3.3 $E_g$ in bulk and QD semiconductors	16
3.4 Different methods of synthesis of nano particles	18
3.5 Mechanism of nano particle production	19
3.6 (A) La Mer's model for the stages of nucleation and growth for monodisperse colloidal particles. (B) Synthetic apparatus contributed in the preparation of monodisperse NQDs. (M. G. Bawendi, 1990)	21
3.7 The different three conditions during the microwave irradiation. (a) is the conductor, (b) is the insulator, and (c) is the dielectric.	23
4.1 Microwave-assisted synthesis of $Zn_xCd_{1-x}S$ semiconductor nanoparticles	27
4.2 Synthesis process of PVP/ TGA capped $Zn_{0.9}Cd_{0.1}S$ nanoparticles	30
4.3 X-ray scattered from atoms	32
4.4 Diagram of a Coolidge tube	32
4.5 Generation of $K\alpha$ X-rays	33
4.6 $\Theta:2\Theta$ goniometer	34
4.8 Geometry of TEM microscope	36
4.9 Geometry of UV-vis spectroscope	38
4.10 Radiative recombination paths: (a) band-to-band; (b) donor to valence band; (c) conduction band to acceptor; (d) Non-radiative recombination via an intermediate state (Gfroerer, 2000)	39
4.11 A typical experimental PL set up	39
5.1 Change the color of $Zn_xCd_{1-x}S$ nanoparticles due to change the formation by increasing the concentration of zinc. a) $x=0.1$ , b) $x=0.3$ , c) $x=0.5$ , d) $x=0.7$ , e) $x=0.9$ .	41
5.2 XRD pattern of $Zn_{0.1}Cd_{0.9}S$ nanoparticle	42
5.3 Comparison of peak list of the $Zn_{0.1}Cd_{0.9}S$ nanoparticles and the reference pattern	43
5.4 XRD pattern of $Zn_{0.3}Cd_{0.7}S$ nanoparticle	44
5.5 Comparison of peak list of $Zn_{0.3}Cd_{0.7}S$ semiconductor nanoparticle with reference pattern	44
5.6 XRD pattern of $Zn_{0.5}Cd_{0.5}S$ nanoparticle	45
5.7 Comparison of peak list of $Zn_{0.5}Cd_{0.5}S$ nanoparticle with reference pattern	45
5.8 XRD pattern of $Zn_{0.7}Cd_{0.3}S$ semiconductor nanoparticle	46
5.9 Comparison of peak list of $Zn_{0.7}Cd_{0.3}S$ nanoparticle with reference pattern	47
5.10 XRD pattern of $Zn_{0.9}Cd_{0.1}S$ semiconductor QD	48
5.11 Comparison of peak list of $Zn_{0.9}Cd_{0.1}S$ nanoparticles with reference pattern	48
5.12 XRD patterns of $Zn_xCd_{1-x}S$ semiconductor nanoparticles with different precursor concentrations. A: $Zn_{0.1}Cd_{0.9}S$ , B: $Zn_{0.3}Cd_{0.7}S$ , C: $Zn_{0.5}Cd_{0.5}S$ , D: $Zn_{0.7}Cd_{0.3}S$ , E: $Zn_{0.9}Cd_{0.1}S$	49
5.13 TEM image and related size distribution histogram of the $Zn_{0.1}Cd_{0.9}S$ nanoparticle	50

5.14 TEM image and related size distribution histogram of the $\text{Zn}_{0.3}\text{Cd}_{0.7}\text{S}$ nanoparticle	51
5.15 TEM image and the related size distribution histogram of $\text{Zn}_{0.5}\text{Cd}_{0.5}\text{S}$ nanoparticle	51
5.16 TEM image and the related size distribution histogram of $\text{Zn}_{0.7}\text{Cd}_{0.3}\text{S}$ nanoparticle	52
5.17 TEM image and the related size distribution histogram of $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticle	52
5.18 UV-vis spectra of $\text{Zn}_x\text{Cd}_{1-x}\text{S}$ nanoparticles.	54
5.19 Tauc plot of $\text{Zn}_x\text{Cd}_{1-x}\text{S}$ nanoparticles. a) $x=0.1$ , b) $x=0.3$ , c) $x=0.5$ , d) $x=0.7$ , e) $x=0.9$	57
5.20 PL spectra of the $\text{Zn}_x\text{Cd}_{1-x}\text{S}$ nanoparticle quantum dots	59
5.21 The XRD pattern of TGA capped $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$	61
5.22 Comparison of peak list of $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticle with reference pattern	61
5.23 TEM image and the related size distribution of $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticles with 1% of TGA	62
5.24 TEM image and the related size distribution of $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticles with 3% of TGA	63
5.25 UV-vis plot with a variation of TGA capped $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ quantum dots	64
5.26 Tauc plot of TGA capped $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ semiconductor nanoparticles, a) TGA=1%, b) TGA=2%, c) TGA=3%, d) TGA=4%, e) TGA=5%	66
5.27 PL spectra for TGA capped $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticles	67
5.28 XRD pattern of PVP capped $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ semiconductor quantum dots	68
5.29 Comparison of the peak list of $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticle with reference pattern	69
5.30 TEM image and related size distribution of $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticle with 1% of PVP	70
5.31 TEM image and related size distribution of $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ nanoparticle with 3% of PVP	70
5.32 UV-vis plot of PVP capped $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ semiconductor quantum dots	71
5.33 Tauc plot of $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ semiconductor nanoparticles with PVP, a) PVP=1%, b) PVP=2%, c) PVP=3%, d) PVP=4%, e) PVP=5%	74
5.34 PL spectra for PVP capped $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$ semiconductor ternary quantum dots	75

## LIST OF ABBREVIATIONS

$\text{CdCl}_2$	Cadmium chloride
LED	Light-emitting diode
$\text{Na}_2\text{S}$	Sodium sulfide
PL	Photoluminescence
PVP	Polyvinylpyrrolidone
QD	Quantum dot
TEM	transmission electron microscope
TGA	Thioglycolic acid
UV-Vis	Ultraviolet-Visible light spectroscopy
XRD	X-ray diffraction
$\text{ZnCl}_2$	Zinc chloride

## LIST OF SYMBOLS

A	Absorbance
$C_p$	Specific heat capacity
$C_s$	Saturated concentration of the ions in the solution
$C_{ss}$	Supersaturated concentration of the ions in the solution
$E_a$	Activation energy
$E_c$	Energy of conduction band
$E_g$	Energy of band gap
$E_v$	Energy of valence band
$E_{rms}^2$	Root mean square of the internal electric field
$f$	Frequency
$G_{l \rightarrow s}$	Free energy change per unit volume when new nuclei are formed from a liquid
$I_0$	Incident light
$I(z)$	Flux density
$J$	Current density
$K$	Rate constant of chemical reaction
$M$	Rest mass of electron
$M^*$	Mass of the particle
$R$	Gas constant
$T$	Absolute temperature
$T_b$	Bulk temperature
$T_i$	Instantaneous temperature
$Z$	Distance
$\alpha_0$	Bohr's radius of hydrogen atom



$\alpha(z)$	Absorbtion coefficient
$\beta$	Line boardening at half maximum intensity
$\gamma$	Specific surface energy of the nucleus
$\varepsilon$	Dielectric constant
$\varepsilon_0$	Dielectric permittivity of free space
$\varepsilon_{\text{eff}}$	Effective relative dielectric loss factor
$\theta$	Bragg angle
$\kappa$	Boltzman's constant
$\lambda_0$	Wavelength of microwave
$v_s$	Volume per molecule in the solid
$\rho$	Density
$\sigma$	Electrical conductivity
$\Phi$	Work function

## CHAPTER 1

### INTRODUCTION

#### 1.1 Background of study

Nanoscience is a wide study area pertaining to diverse methods of synthesis and characterization of nanomaterials such as metal nanoparticles and semiconductor quantum dots- which is a type of nanocrystal made of semiconductor materials that are small enough to exhibit quantum mechanical properties- leading to their high potential applications in medicine, cancer therapy, optical devices, catalysis, and solar cell. Because of their particle size varies in range 1- 100 nm, their electronic parameters are size dependent such that they are promising candidates for optical devices. These types of materials have different electronic and optical properties compared to their bulk material counterparts. Their expanded surface leads to a new atomic arrangement which has an effect on optical properties of nanoparticles. The high surface to volume ratio can cause an increase in surface specific active sites for chemical reactions and photon absorption to enhance reaction and absorption efficiency, and an increase in the surface states, which changes the activity of electrons and holes and affects the chemical reaction dynamics. By decreasing the size of particles, the confinement charge carriers and the quantum size effect can occur, both conduction and valence band can split into discrete electronic states, and the band gap and optical and electronic properties become size dependence.

Ternary chalcogenide-based semiconductor quantum dots have unique size-tunable, optical, and electronic properties. These semiconducting materials have a broad range of applications in photovoltaic devices and solar cells. The Zinc Cadmium Sulfide (ZnCdS) ternary quantum dot is promising candidate as blue emitter and wide bandgap window material in photoconductive devices and heterojunction solar cells.

Among the expand range of nanomaterials, the  $Zn_xCd_{1-x}S$  semiconductor quantum dots (QDs) are the best wide band gap window materials due to its tunable size, shape, and emitting color. To control the shape and size of corresponding QDs many different synthesis methods are presented such as gas-phase process, microwave-assisted hydrothermal method, co-precipitation method, chemical bath deposition, and solvothermal method. The hydrothermal method is useful for the growth of crystals with the ability of good control of their composition. Methods of synthesis the nanoparticles are expected to modify the nanoparticle's surface and properties and form them with narrow size distribution.

#### 1.2 Problem statement

Semiconductor nanoparticles have an important role in new world due to their wide range of applications such as optical devices. In order to use them in technology, their particle size, size distribution, morphology, and optical properties are necessary to be controlled. Recent studies improve the way of synthesis nanoparticles and

introduce some solution to control their properties during the formation process. The optical properties of semiconductor quantum dots are affected by their size distribution and surface that should be controlled to achieve desired optical characters. Some of the synthesis methods cause the large size and unstable particles or require longer hours to complete. Furthermore the products may result in amorphous phase, poor dispersion and with impurities. The microwave-assisted method and capping the nanoparticles with some materials as stabilizer can overcome these problems and give the semiconductor quantum dots with desired properties. In order to use semiconductor nanoparticles in technology, the stability of these materials is very important and can achieve by capping the particles with either organic or inorganic materials like polymers. The utilization of capping agents in nanoparticles synthesis is a way to provide chemical passivation, and improve the surface state that has a significant effect on the optical and electronic properties of nanoparticles. They prevent agglomeration of the nanoparticles and boost their optical properties and stability.

### 1.3 Study objective

In the terms of knowledge creation, this work includes fundamental research of semiconductor QDs synthesis process, effect of precursor's concentration, and also capping agents on physical and optical properties of nanoparticles. In details, in this project the high quality  $\text{Zn}_x\text{Cd}_{1-x}\text{S}$  semiconductor ternary QDs were synthesized via microwave irradiation with  $x$  values of 0.1, 0.3, 0.5, 0.7, and 0.9, and two types of capping agents with concentration from 1% to 5% and characterized to find their properties. To activate successful achievement of these, the thesis research is divided into the following particular objectives:

- 1- To synthesize high purity and quality  $\text{ZnCdS}$  semiconductor ternary QDs by hydrothermal microwave-assisted synthesis process in deionized water as solvent.
- 2- To study the effect of variation of  $x$  ( $x= 0.1$  to  $0.9$ ) of  $\text{Zn}_x\text{Cd}_{1-x}\text{S}$  quantum dot in particle size, size distribution, morphology, and optical properties.
- 3- To investigate the influence of capping agents on synthesis and the growth process of  $\text{Zn}_{0.9}\text{Cd}_{0.1}\text{S}$  semiconductor nanoparticles, and their physical and optical properties.

### 1.4 Scope of study

This work will deal with the important understanding of the synthetic conditions and the surface modification process relation of chalcogenide-based semiconductors. In particular, this thesis prepares and characterizes the  $\text{Zn}_x\text{Cd}_{1-x}\text{S}$  semiconductor QDs to examine their interesting properties and potential for extensive research. The microwave-assisted synthesis method is used to make the semiconductor QDs. Microwave irradiation of precursors decreases the time of reaction from days to minutes and produces smaller particles with a narrow particle size distribution and high purity. With a knowledge of nucleation and growth process, the tuning the size and controlling the shape, structure, and optical properties can be studied. The production of the best quality materials is carried out through selectively isolating

the materials that actively contribute to the most nucleation events followed by efficient growth of the nanoparticles through the use of microwave irradiation. The experimental condition such as concentration of precursors, and the type and concentration of capping agents has also influence in quality of nanoparticles. This thesis is divided into two sections. In the first section the  $Zn_xCd_{1-x}S$  with different values of  $x$  (0.1, 0.3, 0.5, 0.7, and 0.9) was synthesized through the reaction of zinc chloride, cadmium chloride, and sodium sulfide in deionized water as solvent with the aid of microwave radiation as a heating source in order to study the effect of concentration of precursors on the size distribution, optical properties, and morphology of nanoparticles. Second section provides a synthesis process of PVP and TGA capped  $Zn_{0.9}Cd_{0.1}S$  with different concentration of stabilizer from 1% to 5% to monitor the effect of capping agents on the synthesis process, particle size, and size distribution of semiconductor QDs.

### 1.5 Thesis outline

This thesis presents a microwave-assisted hydrothermal synthesis route and characterization of ZnCdS semiconductor ternary QDs with variable concentrations of Zn as one of the precursors, and PVP, and TGA as capping agents. The outline of this thesis comes as follow:

Chapter 1 presents an introduction of this research, including the background of study, problem statement, scope, and objective of the study. Chapter 2 deals with a history of Nanoscience, quantum dot, and chalcogenide  $Zn_xCd_{1-x}S$  semiconductor nanoparticles and related literature in view of the synthesis process of nanoparticles. Chapter 3 is focused on a theory of electronic states of semiconductors and QDs, growth and nucleation process in the synthesis of nanoparticles, and microwave irradiation and its effect on materials. Chapter 4 provides the methodology of this work containing materials, experiment section, and characterization of semiconductor nanoparticles and the related methods. The major part of this thesis has come in Chapter 5 which describes the experimental results and related analysis. The summary and suggestions for future work has presented in last chapter (Chapter 6).

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